

confid  
A1

mixed crystal, reference should be made to the United States Patent 5,352,912.

IN THE CLAIMS

Please amend claim 3 as follows:

3. (Amended) A heterobipolar transistor, comprising:
- a substrate;
  - a collector layer formed on said substrate;
  - a base layer formed on said collector layer; and
  - an emitter layer formed on said base layer,
- said base layer comprising a SiGeC ternary mixed crystal having a C concentration profile such that a C concentration in said base layer increases from a first interface facing said emitter layer to a second interface facing said collector layer,
- wherein said base layer has a Ge concentration substantially constant from said first interface to said second interface.